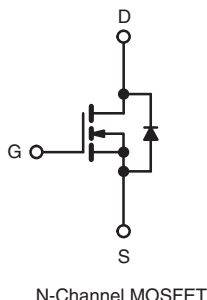
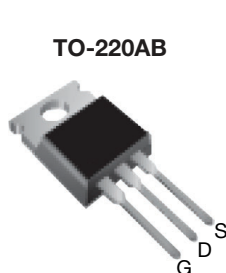


EF Series Power MOSFET with Fast Body Diode

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.098
Q_g (Max.) (nC)	155	
Q_{gs} (nC)	22	
Q_{gd} (nC)	43	
Configuration	Single	



FEATURES

- Fast body diode MOSFET using E series technology
- Reduced t_{rr} , Q_{rr} , and I_{RRM}
- Low figure-of-merit (FOM): $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Telecommunications
 - Server and telecom power supplies
- Lighting
 - High-intensity discharge (HID)
 - Light emitting diodes (LEDs)
- Consumer and computing
 - ATX power supplies
- Industrial
 - Welding
 - Battery chargers
- Renewable energy
 - Solar (PV inverters)
- Switch mode power supplies (SMPS)
 - LLC
 - Phase shifted bridge (ZVS)
 - 3-level inverter
 - AC/DC bridge

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free and Halogen-free	SiHP33N60EF-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 20	
Gate-Source Voltage AC ($f > 1$ Hz)		30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current (Typical) ^a	I_{DM}	100	
Linear Derating Factor		2.2	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	691	mJ
Maximum Power Dissipation	P_D	278	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	dV/dt	$T_J = 125$ °C	V/ns
Reverse Diode dV/dt ^d		20	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DS} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 7$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

**THERMAL RESISTANCE RATINGS**

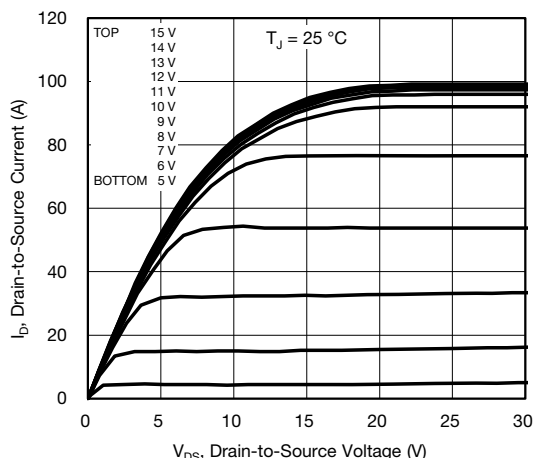
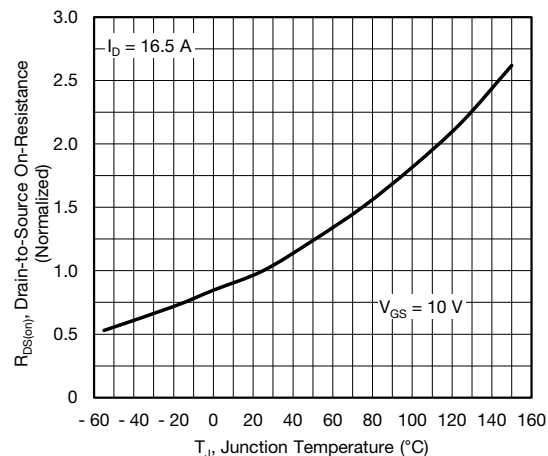
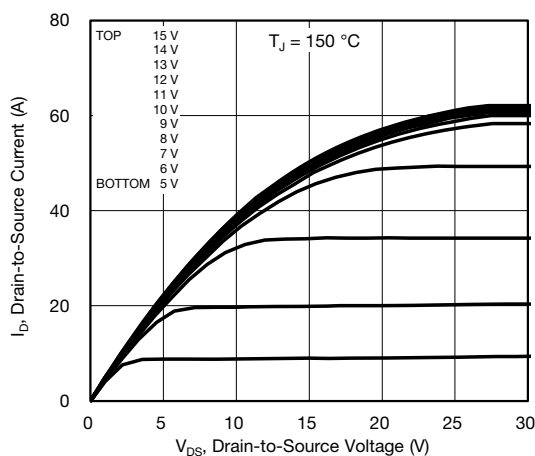
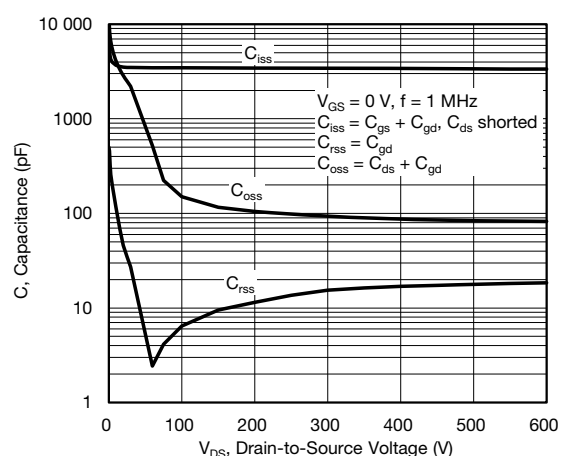
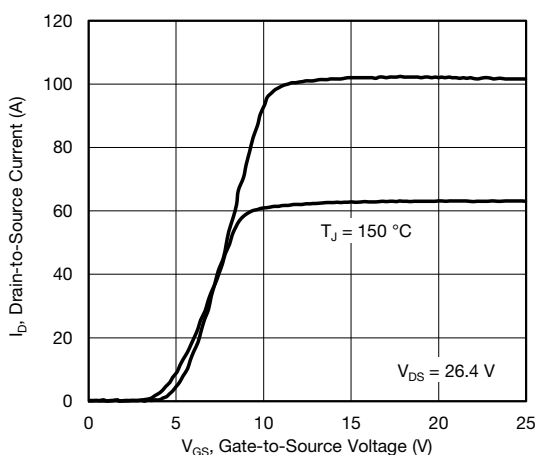
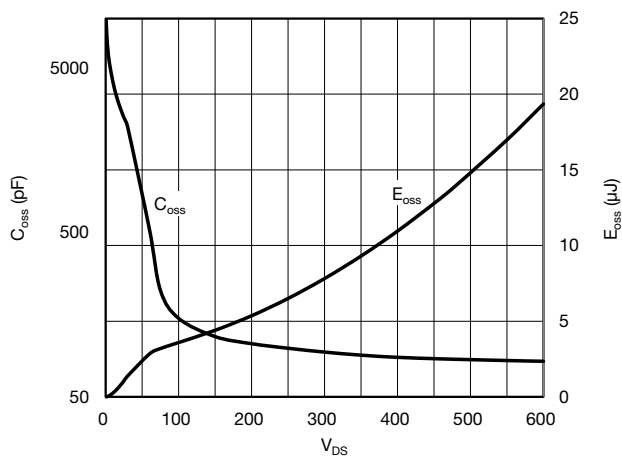
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	

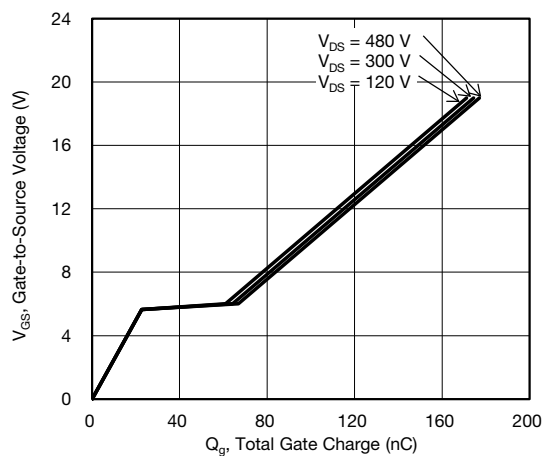
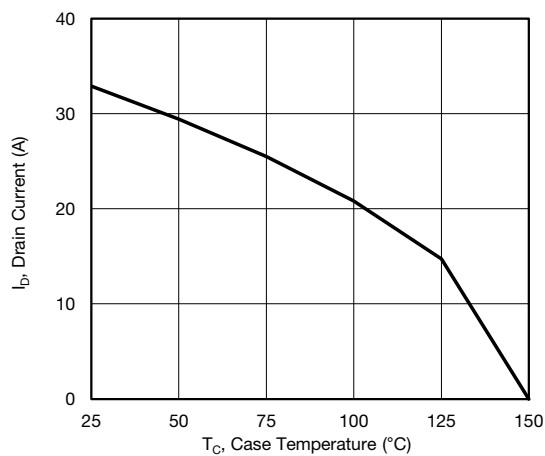
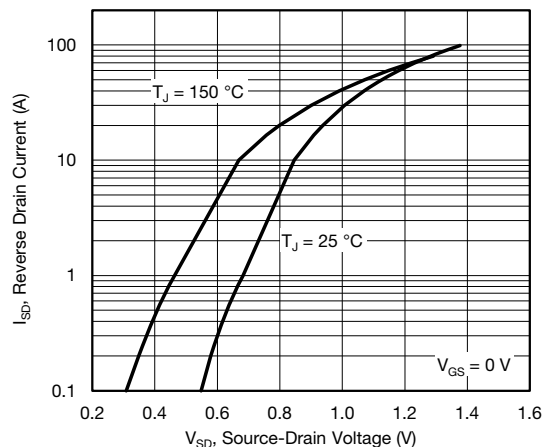
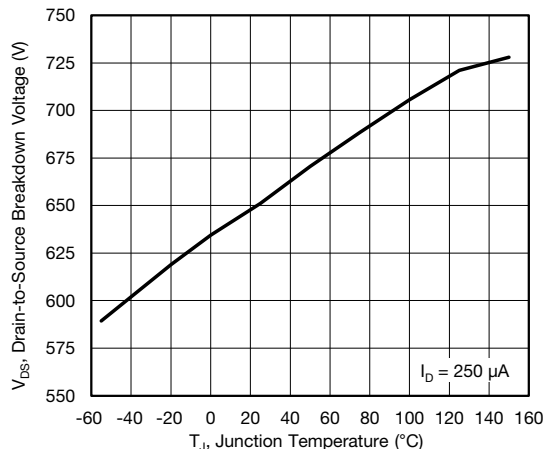
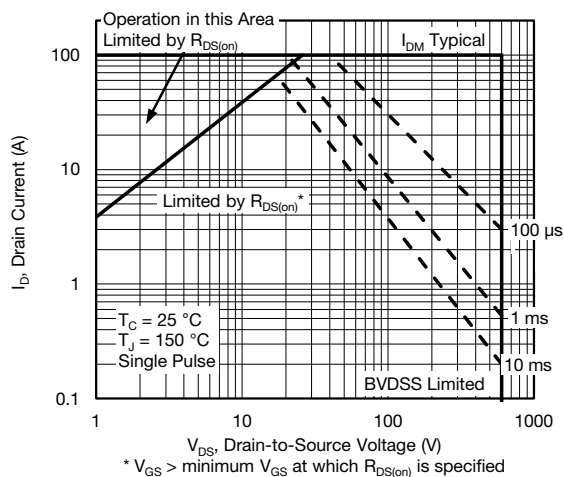
SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

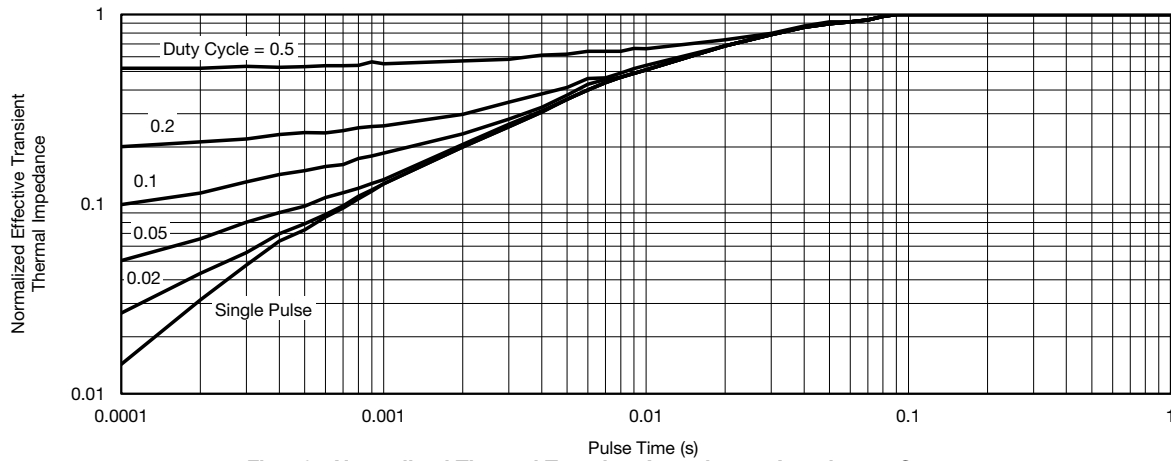
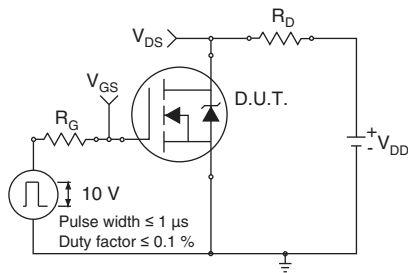
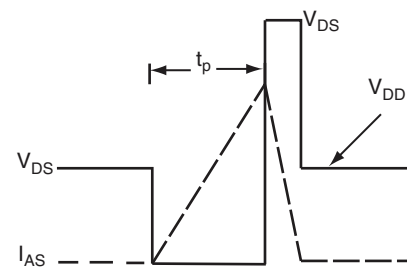
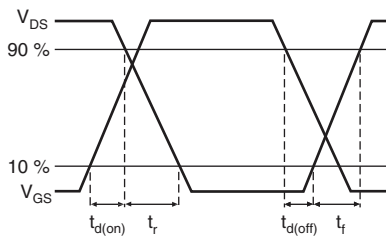
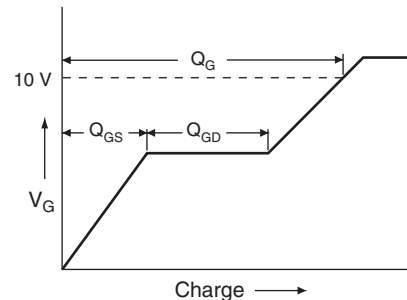
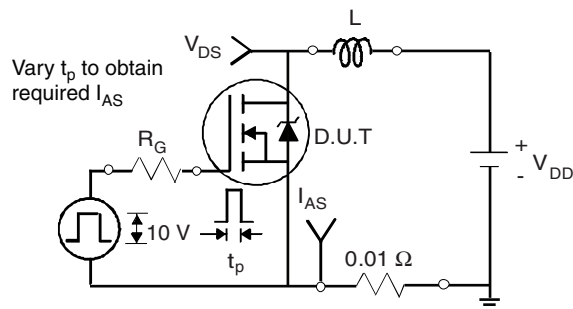
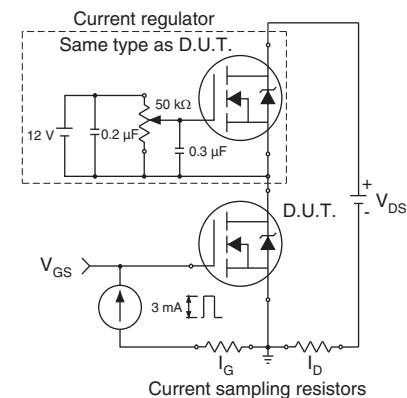
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		600	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.72	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 480 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _J = 125 °C		-	-	500	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 16.5 A	-	0.085	0.098	Ω
Forward Transconductance ^a	g _{fs}	V _{DS} = 30 V, I _D = 16.5 A		-	12	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz		-	3454	-	pF
Output Capacitance	C _{Oss}			-	154	-	
Reverse Transfer Capacitance	C _{rss}			-	8	-	
Effective Output Capacitance, Energy Related ^b	C _{O(er)}	V _{GS} = 0 V, V _{DS} = 0 V to 480 V		-	121	-	
Effective Output Capacitance, Time Related ^c	C _{O(tr)}			-	437	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 16.5 A, V _{DS} = 480 V	-	103	155	nC
Gate-Source Charge	Q _{gs}			-	22	-	
Gate-Drain Charge	Q _{gd}			-	43	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 480 V, I _D = 16.5 A R _g = 9.1 Ω, V _{GS} = 10 V		-	28	56	ns
Rise Time	t _r			-	43	86	
Turn-Off Delay Time	t _{d(off)}			-	161	242	
Fall Time	t _f			-	48	96	
Gate Input Resistance	R _g	f = 1 MHz, open drain		-	0.5	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	33	A
Pulsed Diode Forward Current	I _{SM}			-	100	-	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 16.5 A, V _{GS} = 0 V		-	0.9	1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 16.5 A, dI/dt = 100 A/μs, V _R = 25 V		-	162	324	ns
Reverse Recovery Charge	Q _{rr}			-	1.0	2.0	μC
Reverse Recovery Current	I _{RRM}			-	13	-	A

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature.
b. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
c. $C_{oss(tr)}$ is a fixed capacitance that gives the charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 10 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Typical Source-Drain Diode Forward Voltage

Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature

Fig. 9 - Maximum Safe Operating Area


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

Fig. 13 - Switching Time Test Circuit

Fig. 16 - Unclamped Inductive Waveforms

Fig. 14 - Switching Time Waveforms

Fig. 17 - Basic Gate Charge Waveform

Fig. 15 - Unclamped Inductive Test Circuit

Fig. 18 - Gate Charge Test Circuit


Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 19 - For N-Channel

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